

P3M12160K3 SiC MOS N-Channel Enhancement Mode

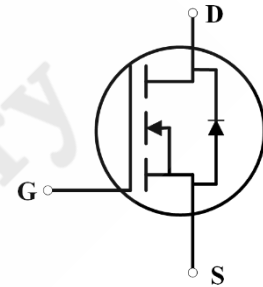
V_{RRM}	= 1200	V
I_D	= 19	A
$I_D (100^\circ\text{C})$	= 13	A
$R_{DS(on)}$	= 160	m Ω

SiC MOS P3M12160K3 N-Channel Enhancement Mode



Features

- Qualified to AEC-Q101
- High Blocking Voltage with Low On-Resistance
- High-Frequency Operation
- Ultra-Small Q_{gd}
- 100% UIS tested



Benefits

- Improve System Efficiency
- Increase Power Density
- Reduce Heat Sink Requirements
- Reduction of System Cost

TO-247-3

Gate	1
Drain	2
Source	3

Application

- Solar Inverters
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies



Order Information

Part number	Package	Marking
P3M12160K3	TO-247-3	P3M12160K3



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1. Maximum Ratings

At $T_J = 25^\circ\text{C}$, unless specified otherwise

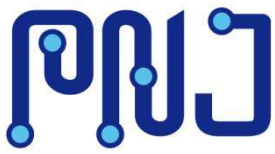
Parameter	Symbol	Value	Unit	Test Conditions
Drain - Source Voltage	V_{DSmax}	1200	V	$V_{GS} = 0V$ $I_D = 100\mu A$
Gate - Source Voltage (dynamic)	V_{GSmax}	-8 / +21	V	AC ($f > 1\text{Hz}$)
Gate - Source Voltage(static) turn-on gate voltage turn-off gate voltage	$V_{GS,on}$ $V_{GS,off}$	+15 / +18 -3	V	Static
Continuous Drain Current	I_D	19	A	$V_{GS} = 15V$ $T_C = 25^\circ\text{C}$
		13		$V_{GS} = 15V$ $T_C = 100^\circ\text{C}$
Power Dissipation	P_D	110	W	
Operating Junction	T_J	-55 To +175	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 To +175	$^\circ\text{C}$	
Solder Temperature	T_L	260	$^\circ\text{C}$	
Mounting Torque	M_d	1 8.8	Nm lbf-in	M3 or 6-32 screw



2. Electrical Characteristics

At $T_J = 25^\circ\text{C}$, unless specified otherwise

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	1200	/	/	V	$V_{GS} = 0V$ $I_D = 100\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	1.8	2.4	/	V	(tested after 30ms pulse at $V_{GS} = 15V$) $V_{DS} = V_{GS}$ $I_D = 2.5mA$ $T_J = 25^\circ\text{C}$
		/	1.6	/	V	$V_{DS} = V_{GS}$ $I_D = 2.5mA$ $T_J = 175^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	/	1.8	500	μA	$V_{GS} = 0V$ $V_{DS} = 1200V$
Gate-Source Leakage Current	I_{GSS}	/	20	250	nA	$V_{GS} = 15V$ $V_{DS} = 0V$
Drain-Source On-State Resistance	$R_{DS(on)}$	/	160	192	m Ω	$V_{GS} = 15V$ $I_D = 10A$ $T_J = 25^\circ\text{C}$
		/	208	/		$V_{GS} = 15V$ $I_D = 10A$ $T_J = 175^\circ\text{C}$
Transconductance	g_{fs}	/	5	/	S	$V_{DS} = 20V$ $I_{DS} = 10A$ $T_J = 25^\circ\text{C}$
		/	4.8	/		$V_{DS} = 20V$ $I_{DS} = 10A$ $T_J = 175^\circ\text{C}$



P3M12160K3 SiC MOS

N-Channel Enhancement Mode

Parameter	Symbol	Value			Unit	Test Conditions
		Min.	Typ.	Max.		
Input Capacitance	C_{iss}	/	1016	/	pF	$V_{GS} = 0V$ $V_{DS} = 800V$ $f = 1MHz$ $V_{AC} = 25mV$
Output Capacitance	C_{oss}	/	36.8	/		
Reverse Transfer Capacitance	C_{rss}	/	3.2	/		
Coss Stored Energy	E_{oss}	/	26.5	/	μJ	
Gate to Source Charge	Q_{gs}	/	11.1	/	nC	$V_{DS} = 800V$ $V_{GS} = -3/15V$ $I_{DS} = 10A$ $I_G = 20mA$
Gate to Drain Charge	Q_{gd}	/	6.1	/		
Total Gate Charge	Q_g	/	27.3	/		

3. Reverse Diode Characteristics

At $T_J = 25^\circ C$, unless specified otherwise

Parameter	Symbol	Value		Unit	Test Conditions
		Typ.	Max.		
Diode Forward Voltage	V_{SD}	5.2	/	V	$V_{GS} = -3V$ $I_{SD} = 5A$ $T_J = 25^\circ C$
		4.8	/	V	$V_{GS} = -3V$ $I_{SD} = 5A$ $T_J = 175^\circ C$
Continuous Diode Forward Current	I_S	13	/	A	$V_{GS} = -3V$

4. Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.36	$^{\circ}C/W$

5. Typical Performance

At $T_J = 25^{\circ}C$, unless specified otherwise

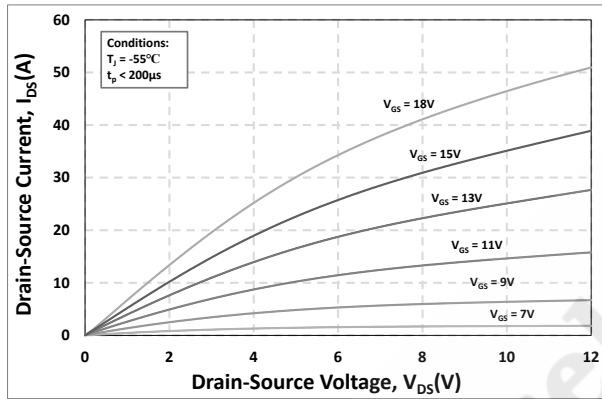


Figure 1. Output Characteristics $T_J = -55^{\circ}C$

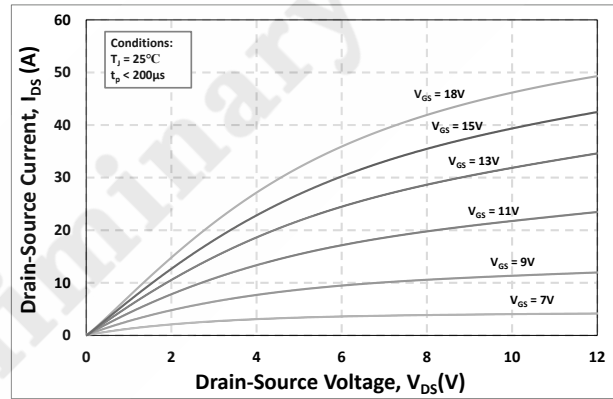


Figure 2. Output Characteristics $T_J = 25^{\circ}C$

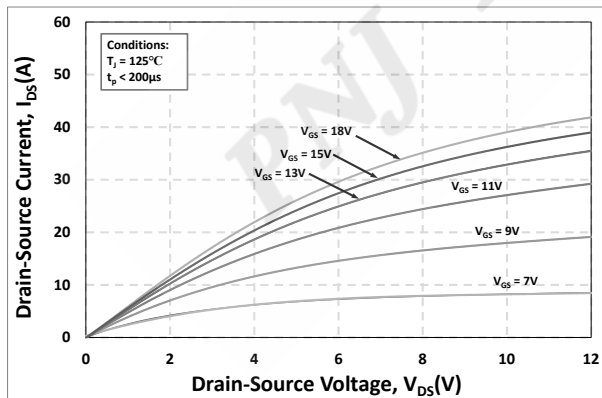


Figure 3. Output Characteristics $T_J = 125^{\circ}C$

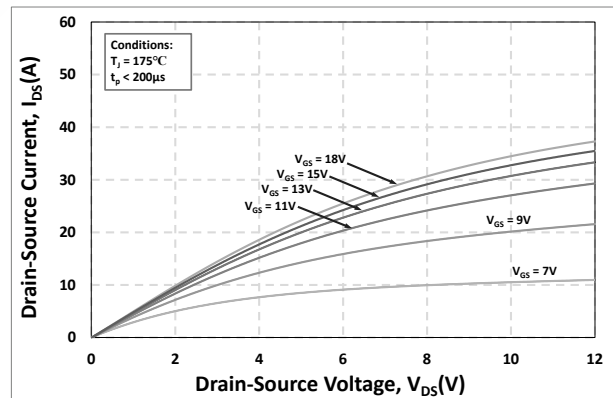


Figure 4. Output Characteristics $T_J = 175^{\circ}C$

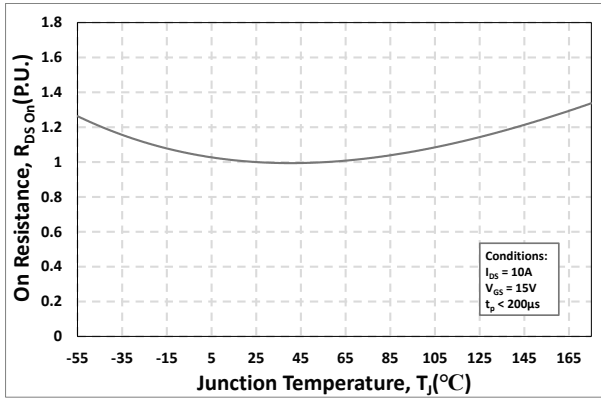


Figure 5. Normalized On-Resistance vs. Temperature

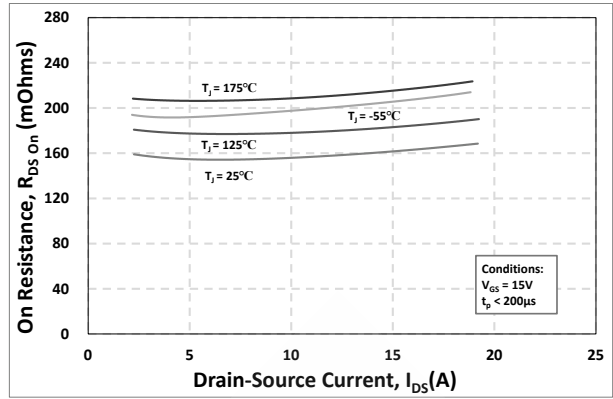


Figure 6. On-Resistance vs. Drain Current Various Temperatures

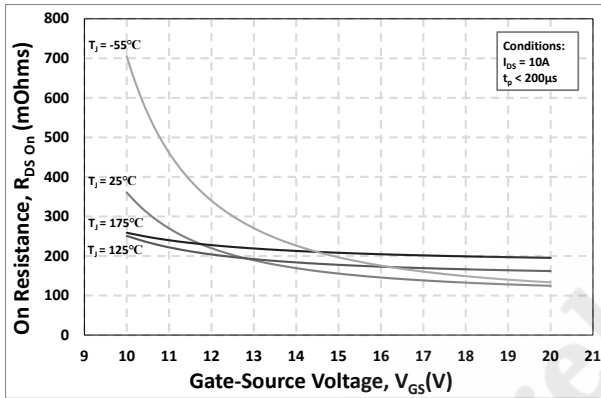


Figure 7. On-Resistance vs. Gate-Source Voltage

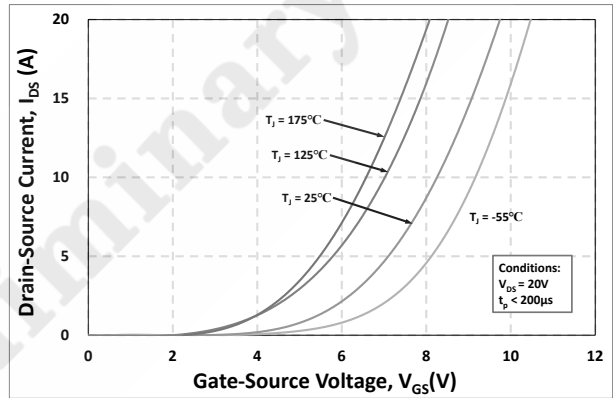


Figure 8. Transfer Characteristic for Various Junction Temperatures

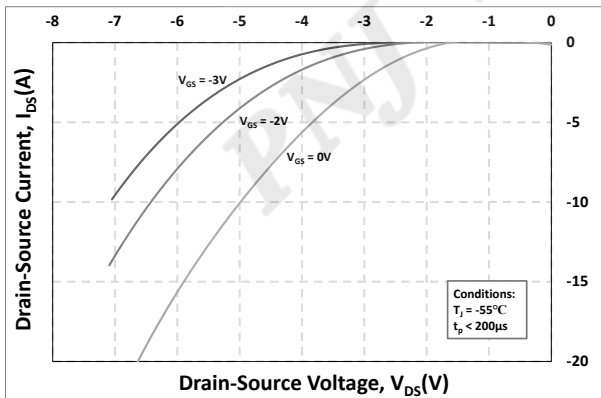


Figure 9. Body Diode Characteristic at -55°C

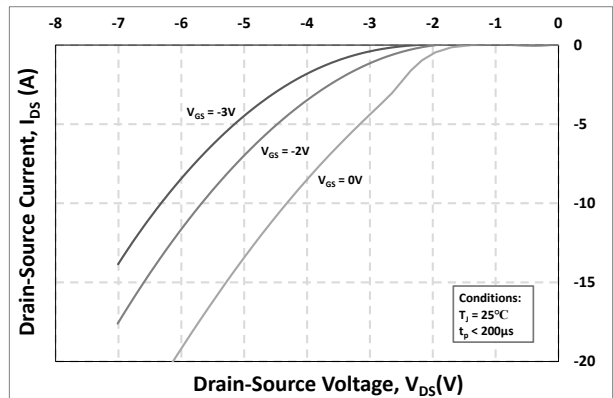


Figure 10. Body Diode Characteristic at 25°C

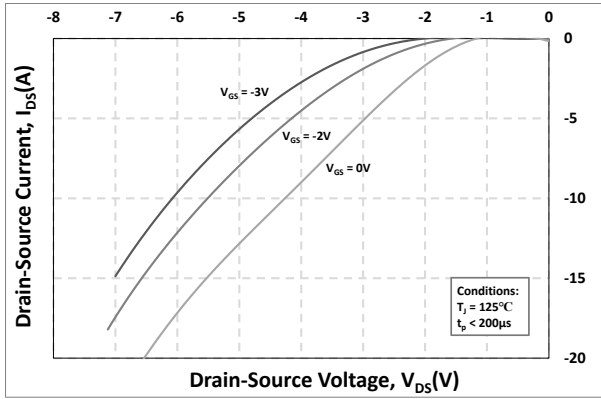


Figure 11. Body Diode Characteristic at 125°C

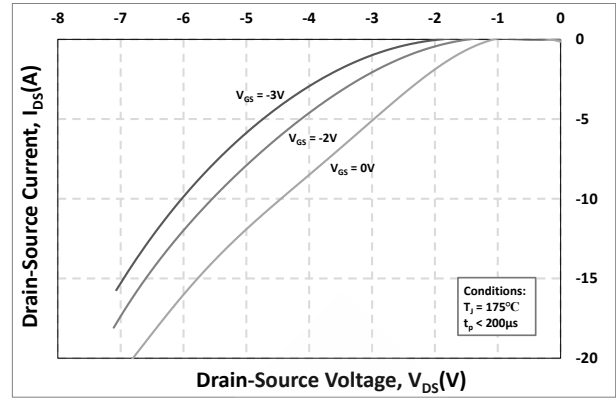


Figure 12. Body Diode Characteristic at 175°C

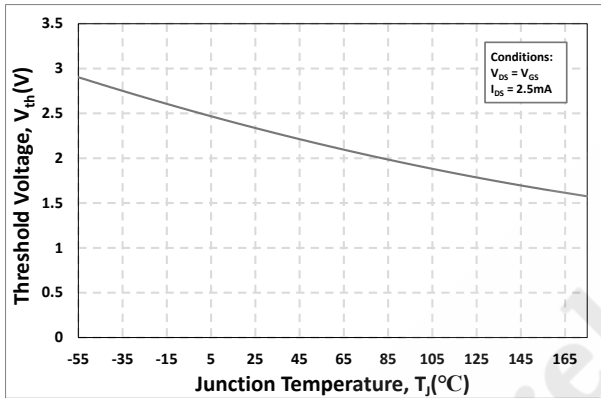


Figure 13. Threshold Voltage vs. Temperature

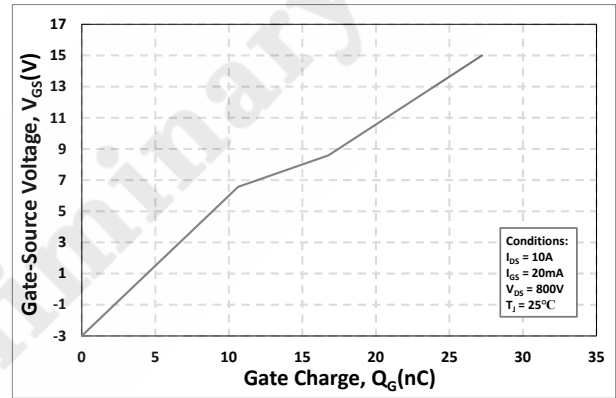


Figure 14. Gate Charge Characteristics

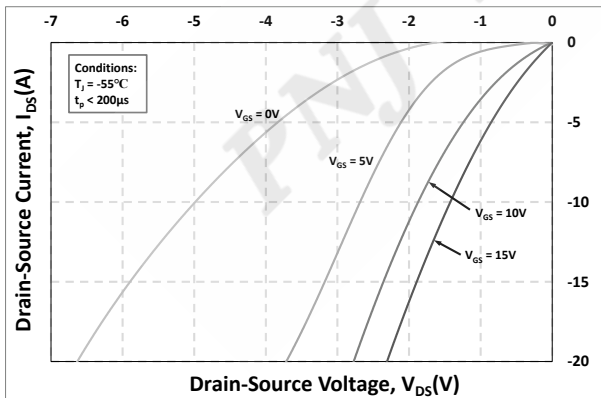


Figure 15. 3rd Quadrant Characteristic at -55°C

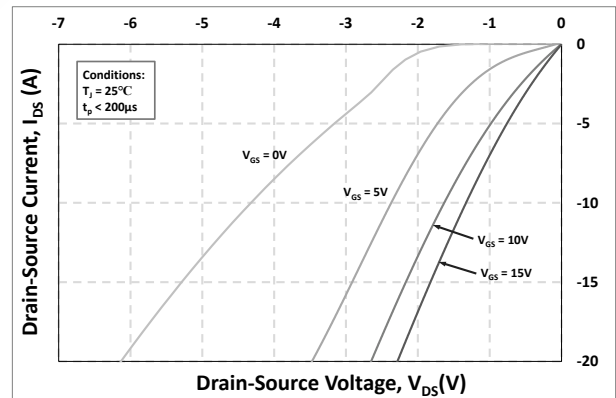


Figure 16. 3rd Quadrant Characteristic at 25°C

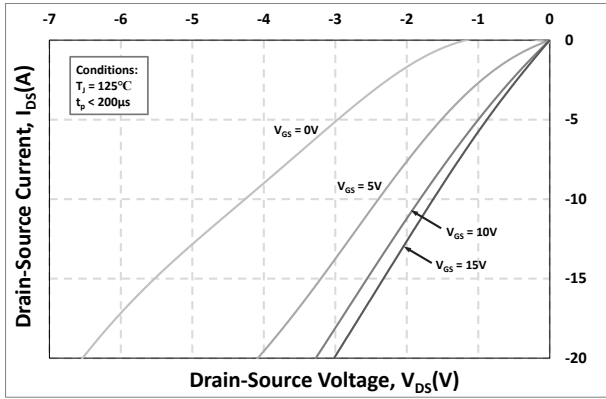


Figure 17. 3rd Quadrant Characteristic at 125°C

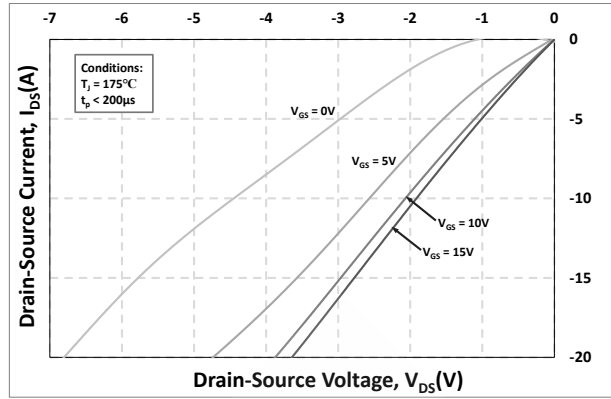


Figure 18. 3rd Quadrant Characteristic at 175°C

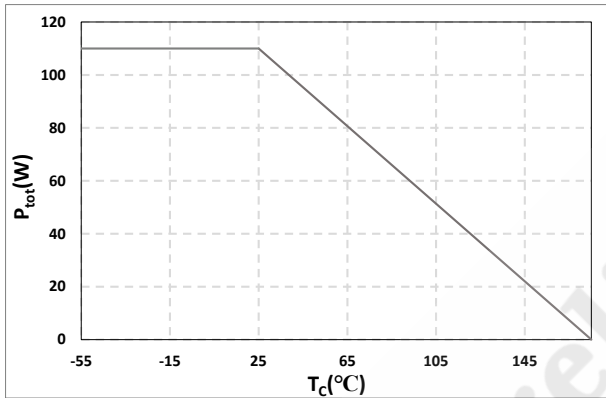


Figure 19. Maximum Power Dissipation Derating vs. Case Temperature

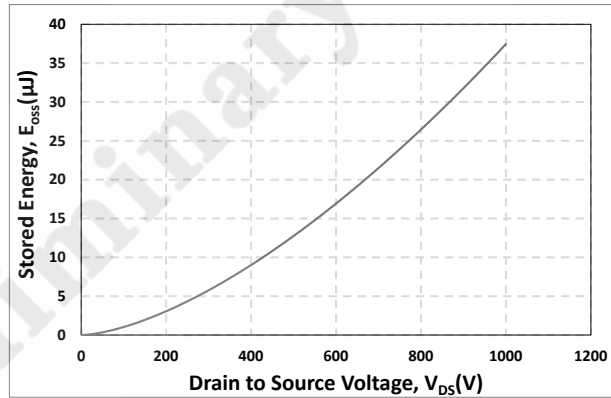


Figure 20. Output Capacitor Stored Energy

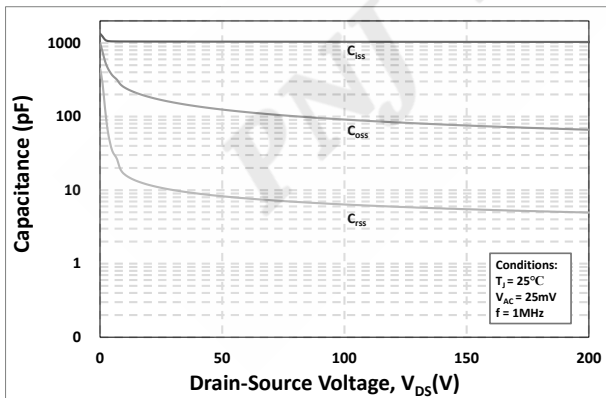


Figure 21. Capacitances vs. Drain-Source Voltage (0 - 200V)

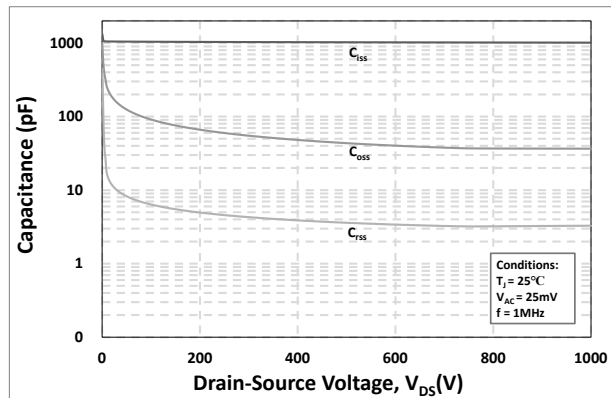


Figure 22. Capacitances vs. Drain-Source Voltage (0 - 1000V)

6. Definitions

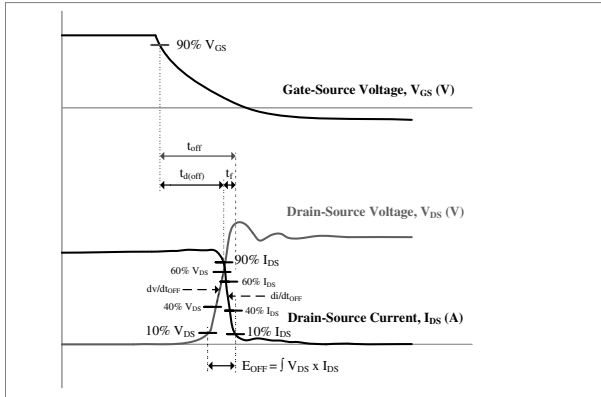


Figure 23. Turn-off Transient Definitions

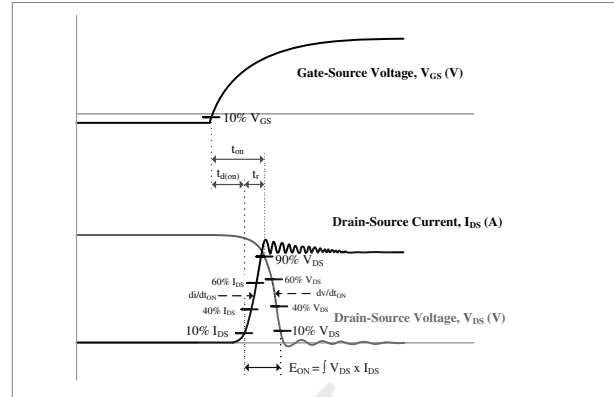


Figure 24. Turn-on Transient Definitions

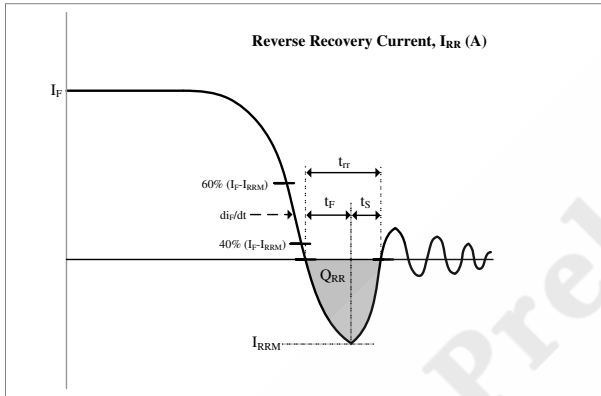


Figure 25. Reverse Recovery Definitions

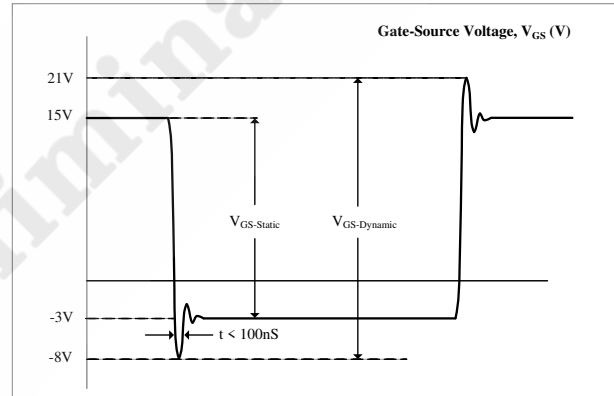
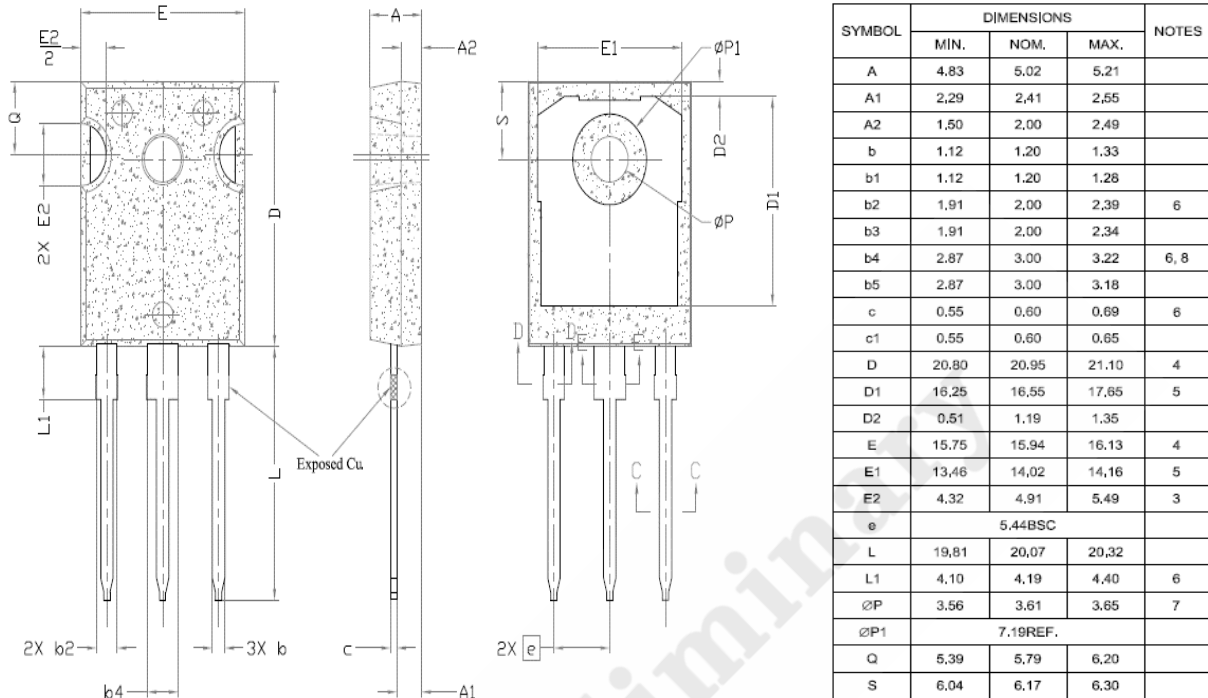


Figure 26. vgs Transient Definitions

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7. Package Outlines



Drawing and Dimensions

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